



# PHPT60410PY

40 V, 10 A PNP high power bipolar transistor

21 January 2015

Product data sheet

## 1. General description

PNP high power bipolar transistor in a SOT669 (LFPK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT60410NY

## 2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

## 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-40	V
$I_C$	collector current		-	-	-10	A
$I_{CM}$	peak collector current	$t_p \leq 1$ ms; single pulse	-	-	-20	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = -10$ A; $I_B = -1$ A; pulsed; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ; $T_{amb} = 25$ °C	-	37	55	m $\Omega$

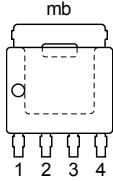
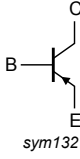


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 <p><b>LFPAK56; Power-SO8 (SOT669)</b></p>	
2	E	emitter		
3	E	emitter		
4	B	base		
mb	C	collector		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHPT60410PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60410PY	0410PAB

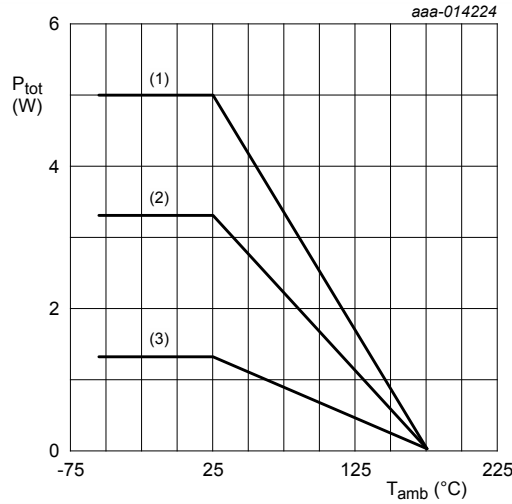
## 8. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-40	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-8	V
I <sub>C</sub>	collector current			-	-10	A
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; single pulse		-	-20	A
I <sub>B</sub>	base current			-	-1	A
I <sub>BM</sub>	peak base current	t <sub>p</sub> ≤ 1 ms; pulsed		-	-2	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.3	W
			[2]	-	3.3	W
			[3]	-	5	W
			[4]	-	25	W
T <sub>j</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W
			[2]	-	-	45	K/W
			[3]	-	-	30	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

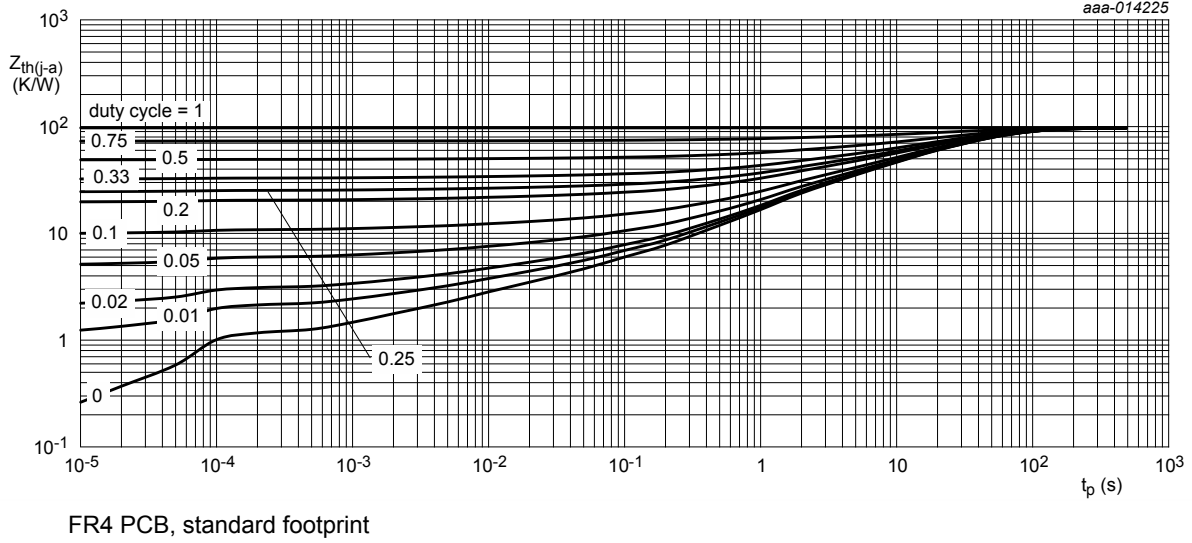


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

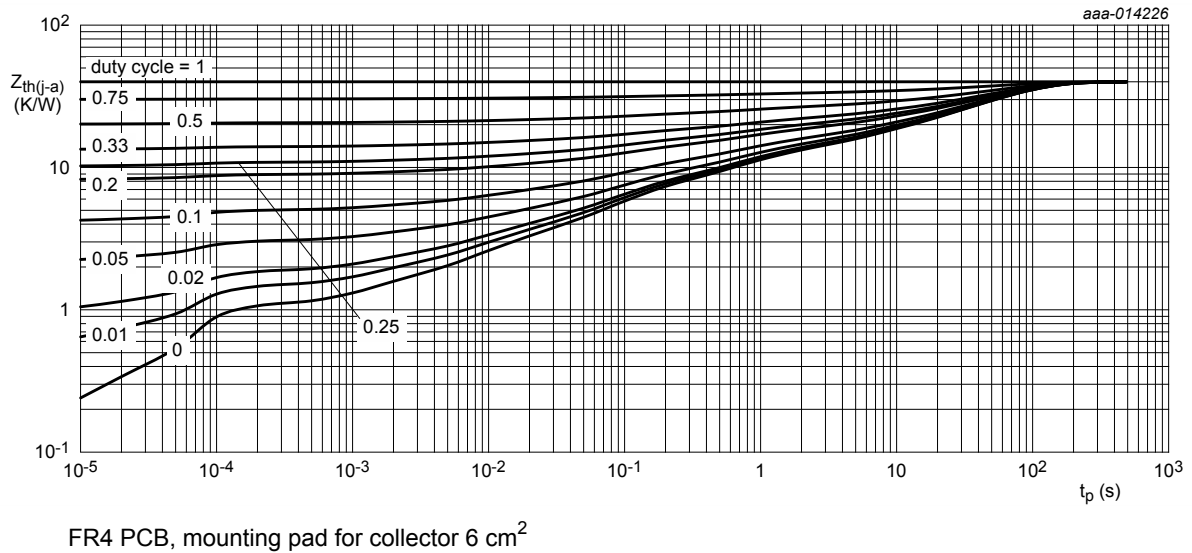


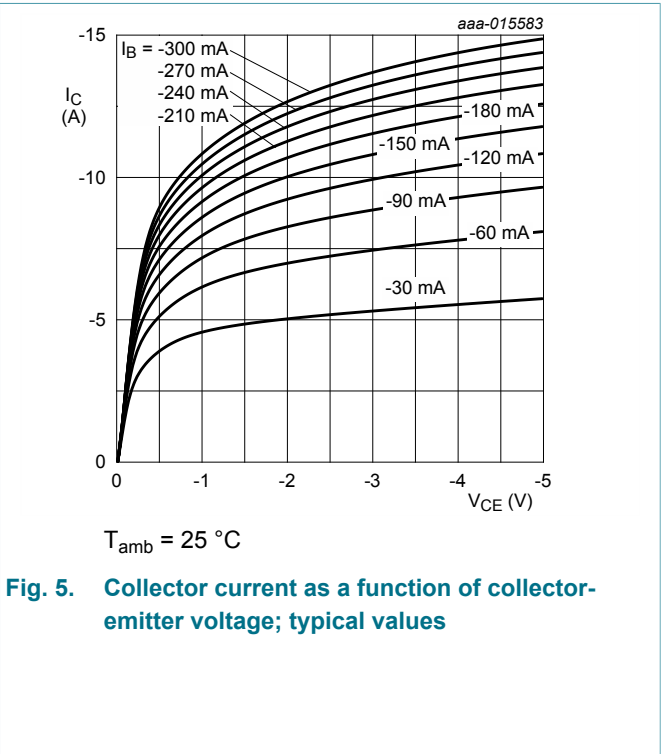
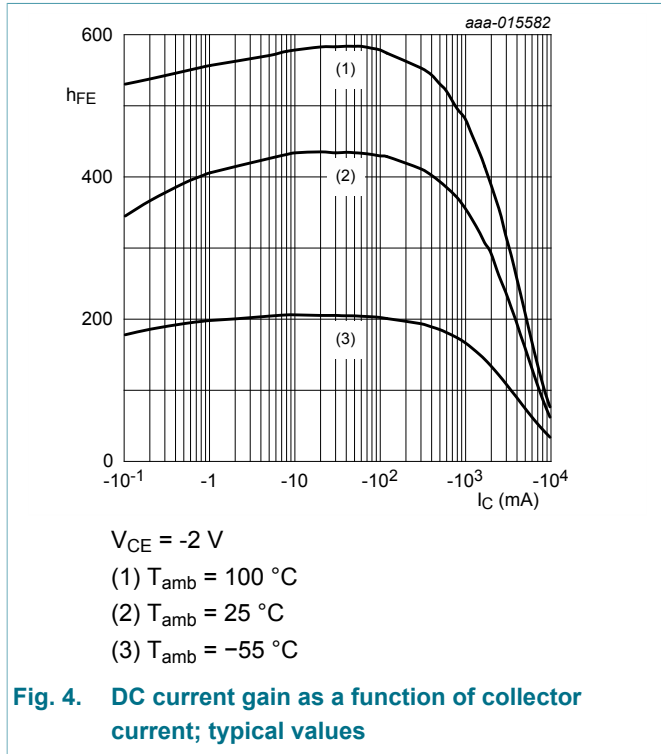
Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = -32 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
		V <sub>CB</sub> = -32 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -32 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -8 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	240	350	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -1 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	220	320	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -5 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	100	150	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -10 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	40	50	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-50	-70	mV
		I <sub>C</sub> = -5 A; I <sub>B</sub> = -500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-180	-250	mV
		I <sub>C</sub> = -10 A; I <sub>B</sub> = -500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-550	-800	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -10 A; I <sub>B</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	37	55	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-0.95	V
		I <sub>C</sub> = -5 A; I <sub>B</sub> = -500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-1.15	V
		I <sub>C</sub> = -10 A; I <sub>B</sub> = -500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-1.25	V
V <sub>BEon</sub>	base-emitter turn-on voltage	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	-	-	-0.8	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -12.5 V; I <sub>C</sub> = -5 A; I <sub>Bon</sub> = -250 mA; I <sub>Boff</sub> = 250 mA; T <sub>amb</sub> = 25 °C	-	15	-	ns
t <sub>r</sub>	rise time		-	105	-	ns
t <sub>on</sub>	turn-on time		-	120	-	ns
t <sub>s</sub>	storage time		-	155	-	ns
t <sub>f</sub>	fall time		-	80	-	ns
t <sub>off</sub>	turn-off time		-	235	-	ns

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_T$	transition frequency	$V_{CE} = -10\text{ V}; I_C = -500\text{ mA};$ $f = 100\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	-	97	-	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A};$ $f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	-	84	-	pF



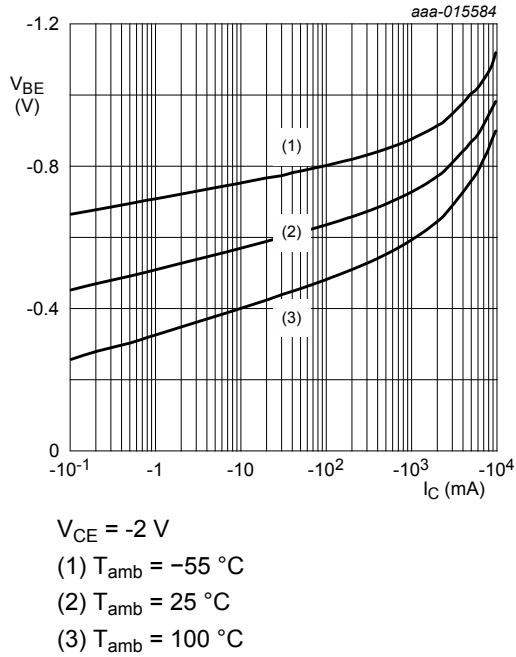


Fig. 6. Base-emitter voltage as a function of collector current; typical values

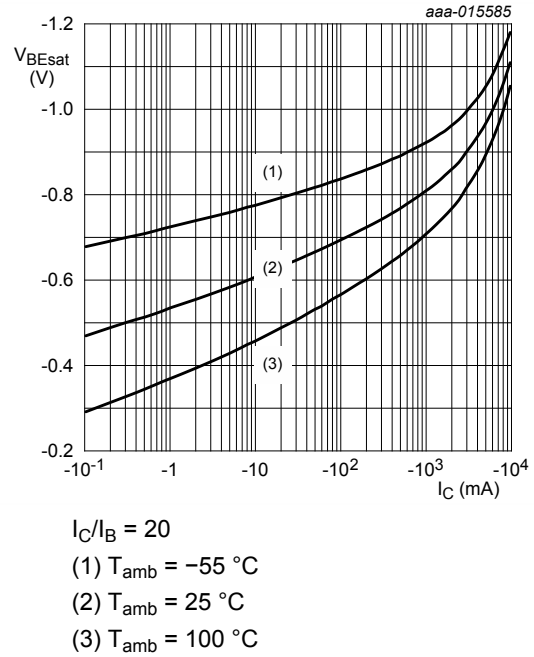


Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

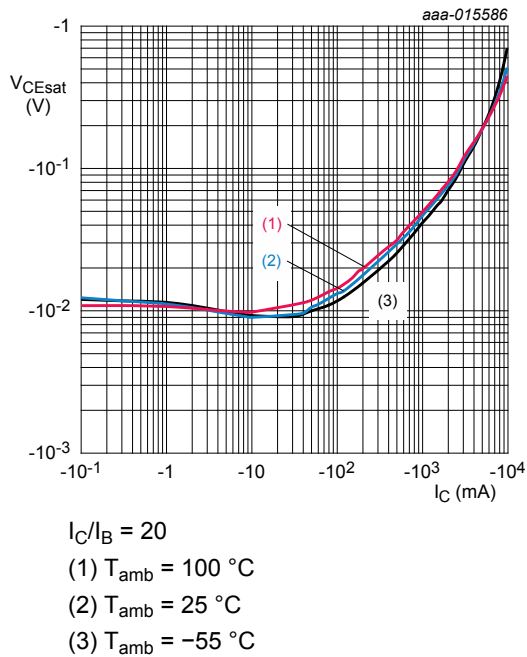


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

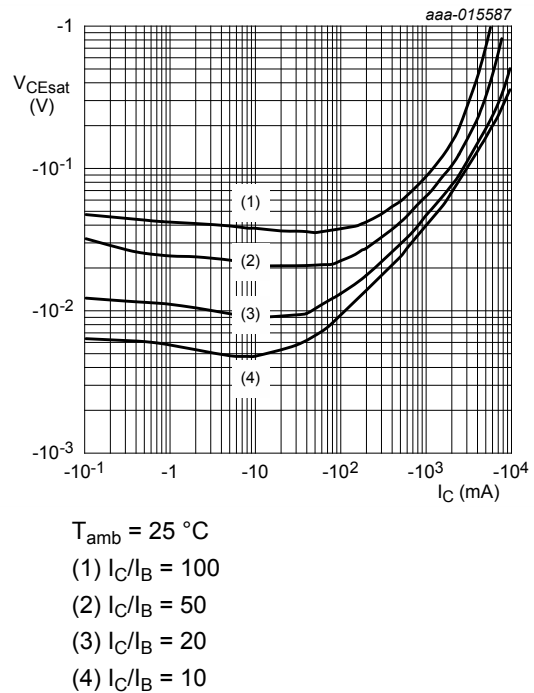
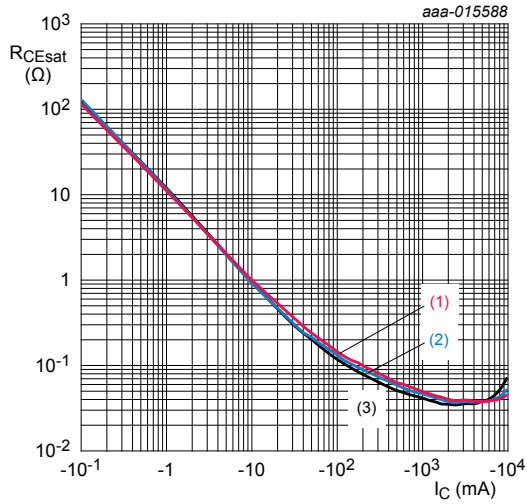


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

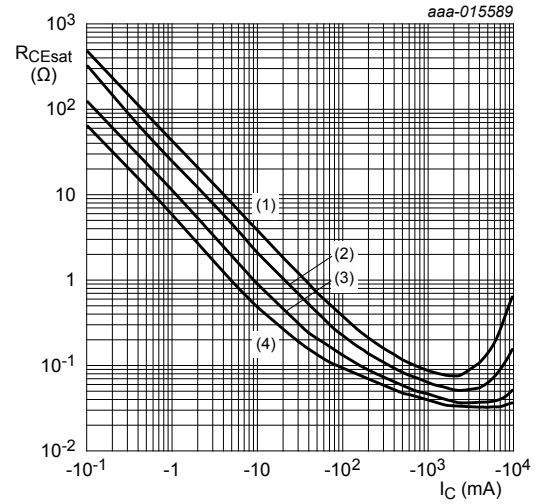




$I_C/I_B = 20$

- (1)  $T_{amb} = 100\text{ °C}$
- (2)  $T_{amb} = 25\text{ °C}$
- (3)  $T_{amb} = -55\text{ °C}$

**Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values**



$T_{amb} = 25\text{ °C}$

- (1)  $I_C/I_B = 100$
- (2)  $I_C/I_B = 50$
- (3)  $I_C/I_B = 20$
- (4)  $I_C/I_B = 10$

**Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values**

### 11. Test information

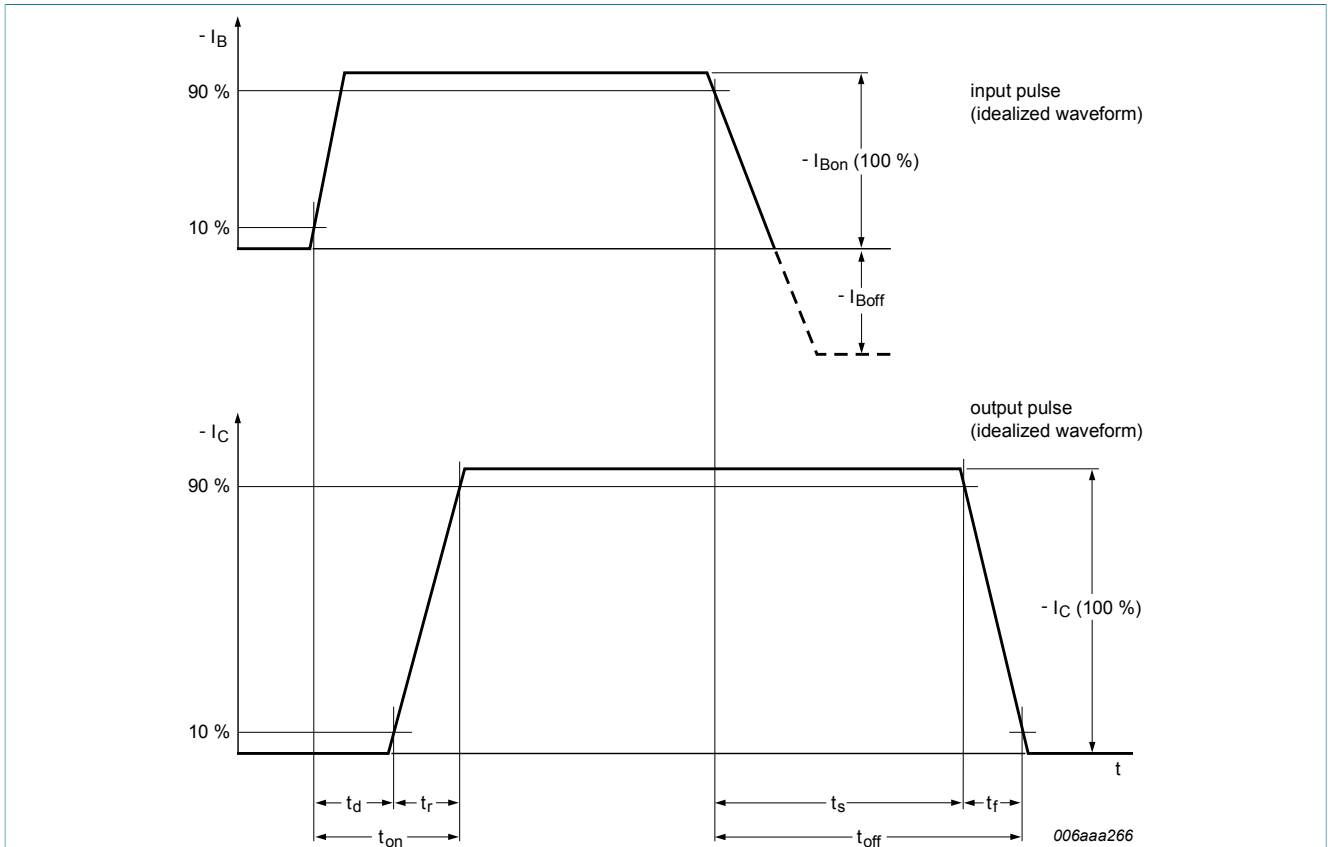


Fig. 12. BISS transistor switching time definition

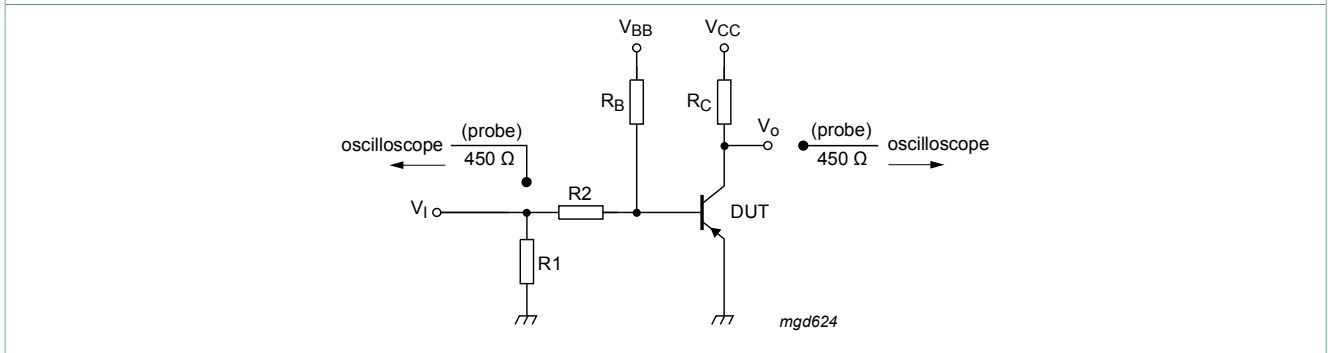


Fig. 13. Test circuit for switching times

#### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

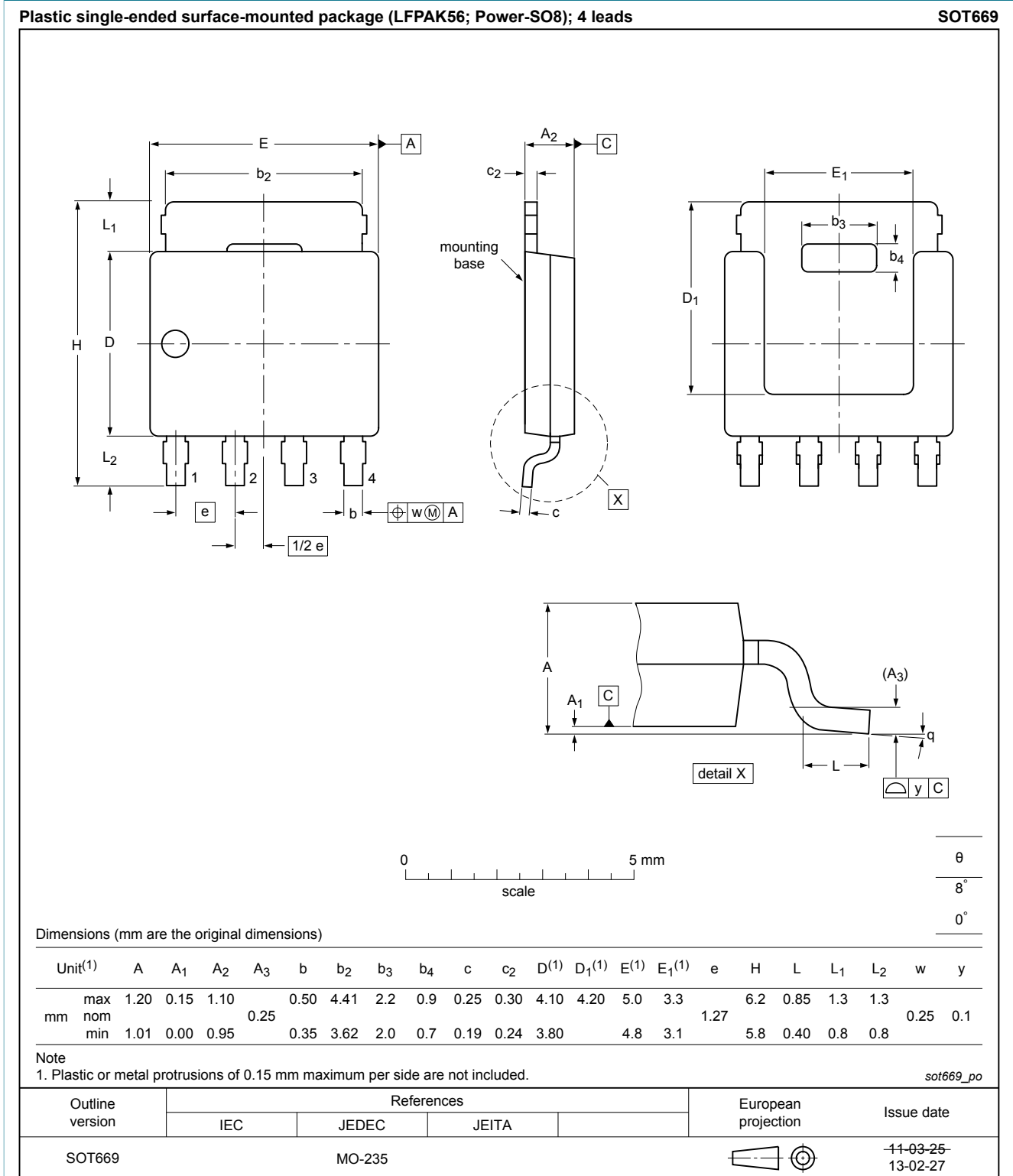


Fig. 14. Package outline LFAK56; Power-SO8 (SOT669)

### 13. Soldering

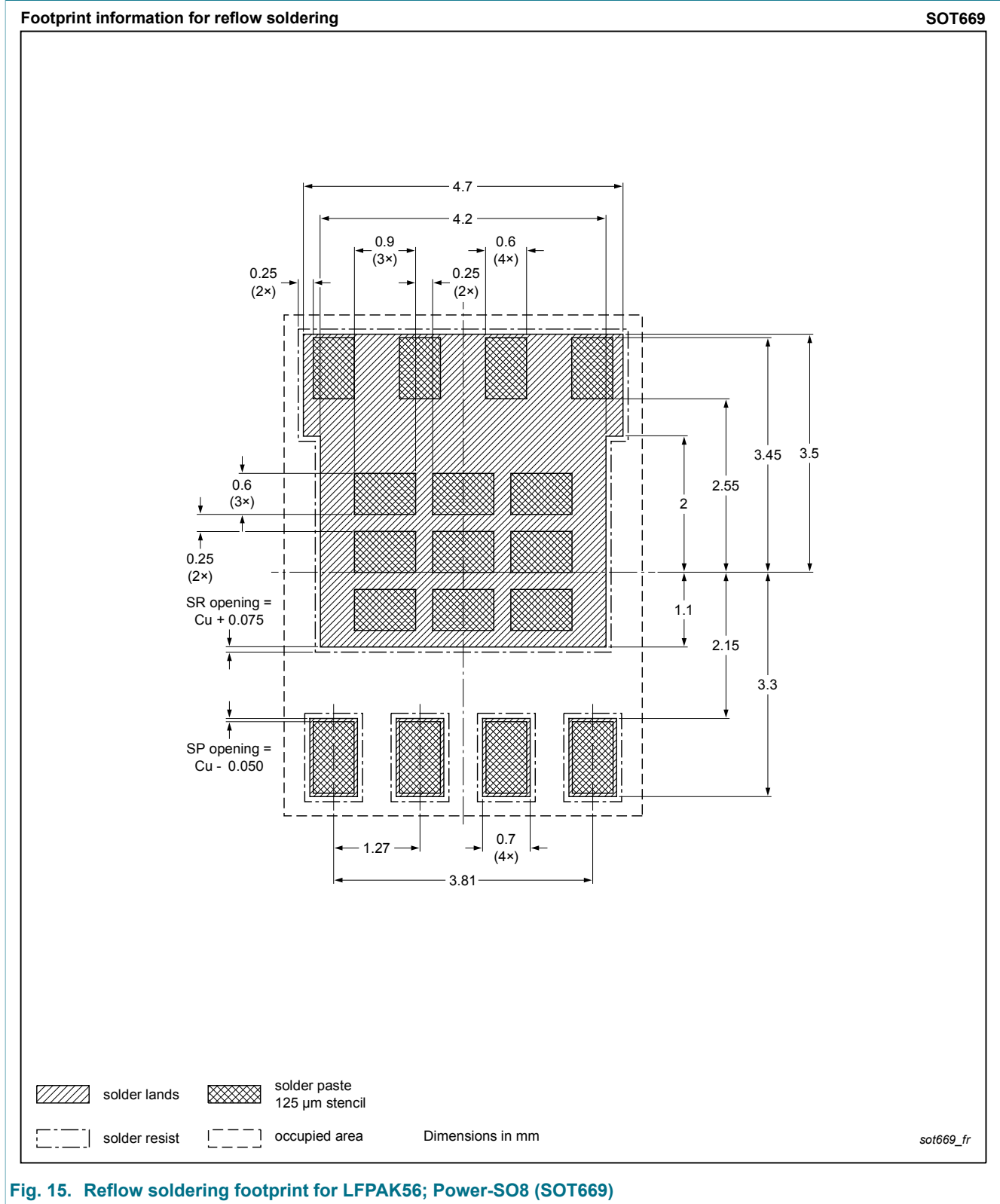


Fig. 15. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60410PY v.1	20150121	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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